

N-channel LFPAK 100 V 39.5 mΩ standard level MOSFET

Rev. 02 — 2 April 2010

**Product data sheet** 

### 1. Product profile

#### 1.1 General description

Standard level N-channel MOSFET in LFPAK package qualified to 175 °C. This product is designed and qualified for use in a wide range of industrial, communications and domestic equipment.

#### 1.2 Features and benefits

- Advanced TrenchMOS provides low RDSon and low gate charge
- High efficiency gains in switching power converters

#### **1.3 Applications**

- DC-to-DC converters
- Lithium-ion battery protection
- Load switching

#### 1.4 Quick reference data

#### Table 1. Quick reference

- Improved mechanical and thermal characteristics
- LFPAK provides maximum power density in a Power SO8 package
- Motor control
- Server power supplies

Table 1.	QUICK reference					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 175 °C	-	-	100	V
I <sub>D</sub>	drain current	T <sub>mb</sub> = 25 °C; V <sub>GS</sub> = 10 V; see <u>Figure 1</u>	-	-	28.1	А
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; see <u>Figure 2</u>	-	-	74	W
Tj	junction temperature		-55	-	175	°C
Avalanc	he ruggedness					
E <sub>DS(AL)S</sub>	non-repetitive drain-source avalanche energy		-	-	42	mJ
Dynamic	characteristics					
Q <sub>GD</sub>	gate-drain charge	$V_{GS} = 10 \text{ V}; I_D = 15 \text{ A};$	-	8	-	nC
Q <sub>G(tot)</sub>	total gate charge	$V_{DS} = 50 V;$ see Figure 14 and 15	-	23	-	nC

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Table 1.	Quick reference	.continued				
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static c	haracteristics					
R <sub>DSon</sub>	drain-source on-state resistance	$\label{eq:VGS} \begin{array}{l} V_{GS} = 10 \text{ V}; \text{ I}_{D} = 15 \text{ A}; \\ T_{j} = 100 \text{ °C}; \text{ see } \overline{Figure \ 12} \end{array}$	-	-	71	mΩ
		$\label{eq:VGS} \begin{array}{l} V_{GS} = 10 \text{ V}; \text{ I}_{D} = 15 \text{ A}; \\ T_{j} = 25 \text{ °C}; \text{ see } \underline{\text{Figure 13}} \end{array}$	-	30.8	39.5	mΩ

### 2. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S	source		-
2	S	source	mb	
3	S	source		
4	G	gate	Q	
mb	D	mounting base; connected to drain		mbb076 S
			SOT669 (LFPAK)	

### 3. Ordering information

Table 3. Ordering information					
Type number	Package				
	Name	Description	Version		
PSMN039-100YS	LFPAK	plastic single-ended surface-mounted package (LFPAK); 4 leads	SOT669		

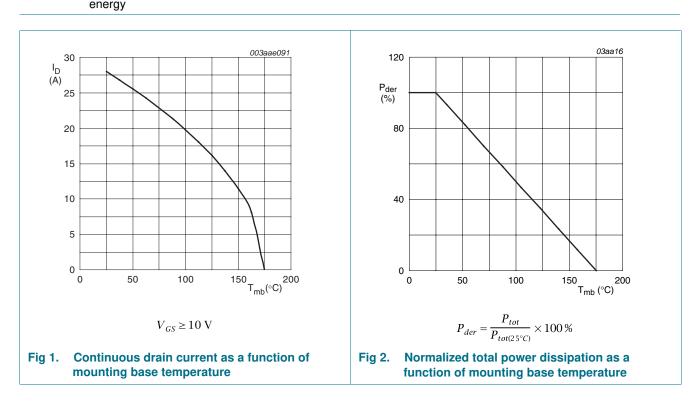
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### 4. Limiting values

#### Table 4. Limiting values

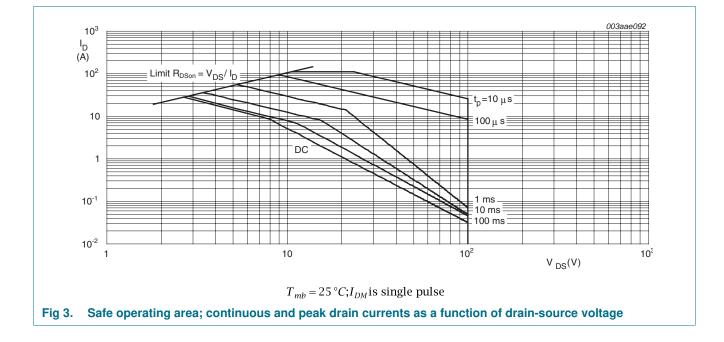
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 175 °C	-	100	V
V <sub>DGR</sub>	drain-gate voltage	$T_j \le 175 \text{ °C}; T_j \ge 25 \text{ °C}; R_{GS} = 20 \text{ k}\Omega$	-	100	V
V <sub>GS</sub>	gate-source voltage		-20	20	V
I <sub>D</sub>	drain current	$V_{GS}$ = 10 V; $T_{mb}$ = 100 °C; see <u>Figure 1</u>	-	20	А
		$V_{GS}$ = 10 V; $T_{mb}$ = 25 °C; see <u>Figure 1</u>	-	28.1	А
I <sub>DM</sub>	peak drain current	$t_p \le 10 \ \mu s$ ; pulsed; $T_{mb} = 25 \ ^{\circ}C$ ; see Figure 3	-	112	А
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; see <u>Figure 2</u>	-	74	W
T <sub>stg</sub>	storage temperature		-55	175	°C
Tj	junction temperature		-55	175	°C
$T_{sld(M)}$	peak soldering temperature		-	260	°C
Source-dr	ain diode				
ls	source current	T <sub>mb</sub> = 25 °C	-	28.1	А
I <sub>SM</sub>	peak source current	$t_p \le 10 \ \mu s$ ; pulsed; $T_{mb} = 25 \ ^{\circ}C$	-	112	А
Avalanche	e ruggedness				
E <sub>DS(AL)S</sub>	non-repetitive drain-source avalanche energy	$      V_{GS} = 10 \text{ V};  \text{T}_{j(init)} = 25 \text{ °C};  \text{I}_{\text{D}} = 28.1 \text{ A}; \\       \text{V}_{\text{sup}} \leq 100 \text{ V}; \text{ unclamped};  \text{R}_{\text{GS}} = 50  \Omega $	-	42	mJ



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### 5. Thermal characteristics

Parameter	Conditions			Min	Тур	Max	Unit
thermal resistance from junction to mounting base	see <u>Figure 4</u>			-	1	2.03	K/W
						003aae093	
- δ = 0.5							
0.2							
0.05				P		$\delta = \frac{t_p}{T}$	
single shot							
-6 10 <sup>-5</sup>	10 <sup>-4</sup>	10 <sup>-3</sup>	10 <sup>-2</sup>	10			
	base δ = 0.5 0.2 0.1 0.05 0.02 single shot	base $\delta = 0.5$ 0.2 0.1 0.05 0.02	base δ = 0.5 0.2 0.1 0.05 0.02 single shot	base $\delta = 0.5$ 0.2 0.1 0.05 0.02 single shot	base δ = 0.5 0.2 0.1 0.05 0.02 single shot	base $\delta = 0.5$ 0.2 0.1 0.5 0.2 0.1 0.5 0.2 0.1 0.5 0.2 0.1 0.5 0.2 0.1 0.5 0.2 0.1 0.5 0.2 0.1 0.5 0.2 0.1 0.5 0.2 0.1 0.5 0.2 0.1	base $0.3ae093$ $\delta = 0.5$ $0.2$ $0.1$ $0.5$ $0.2$ $0.1$ $0.5$ $0.2$ $0.1$ $0.5$ $0.2$ $0.1$ $0.5$ $0.2$ $0.1$ $0.5$ $0.2$ $0.1$ $0.5$ $0.2$ $0.1$ $0.5$ $0.2$ $0.1$ $0.5$ $0.2$ $0.1$ $0.5$ $0.2$ $0.1$ $0.5$ $0.2$ $0.1$ $0.5$ $0.2$ $0.1$ $0.5$ $0.2$ $0.1$ $0.5$ $0.2$ $0.1$ $0.5$ $0$

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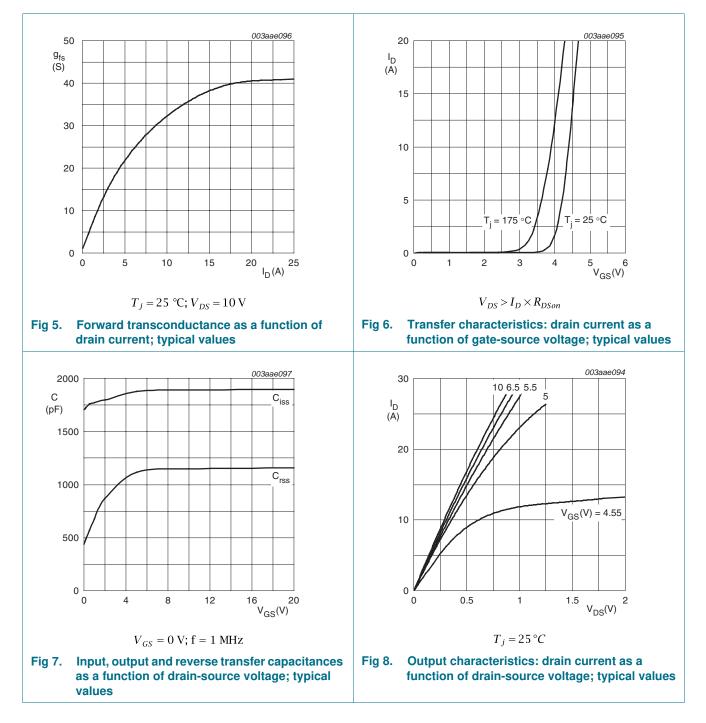
### 6. Characteristics

Table 6.	Characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	racteristics					
V <sub>(BR)DSS</sub>	drain-source	$I_D$ = 0.25 mA; $V_{GS}$ = 0 V; $T_j$ = -55 °C	90	-	-	V
	breakdown voltage	$I_D = 0.25 \text{ mA}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	100	-	-	V
$V_{GS(th)}$	GS(th) gate-source threshold voltage	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 175 \text{ °C};$ see <u>Figure 10</u>	1	-	-	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ °C};$ see <u>Figure 11</u> and <u>10</u>	2	3	4	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ °C};$ see <u>Figure 10</u>	-	-	4.7	V
I <sub>DSS</sub>	drain leakage current	$V_{DS}$ = 100 V; $V_{GS}$ = 0 V; $T_j$ = 125 °C	-	-	50	μA
		$V_{DS}$ = 100 V; $V_{GS}$ = 0 V; $T_j$ = 25 °C	-	0.01	2	μA
I <sub>GSS</sub>	gate leakage current	$V_{GS}$ = 20 V; $V_{DS}$ = 0 V; $T_j$ = 25 °C	-	2	100	nA
		$V_{GS}$ = -20 V; $V_{DS}$ = 0 V; $T_j$ = 25 °C	-	2	100	nA
R <sub>DSon</sub>	DSon drain-source on-state resistance	$V_{GS}$ = 10 V; $I_D$ = 15 A; $T_j$ = 100 °C; see <u>Figure 12</u>	-	-	71	mΩ
	V <sub>GS</sub> = 10 V; I <sub>D</sub> = 15 A; T <sub>j</sub> = 175 °C; see <u>Figure 12</u>	-	72.9	100	mΩ	
		$V_{GS}$ = 10 V; I <sub>D</sub> = 15 A; T <sub>j</sub> = 25 °C; see <u>Figure 13</u>	-	30.8	39.5	mΩ
R <sub>G</sub>	internal gate resistance (AC)	f = 1 MHz	-	0.62	1.5	Ω
Dynamic	characteristics					
Q <sub>G(tot)</sub>	total gate charge	$I_D$ = 15 A; $V_{DS}$ = 50 V; $V_{GS}$ = 10 V; see <u>Figure 14</u> and <u>15</u>	-	23	-	nC
		$I_D = 0 \text{ A}; \text{ V}_{DS} = 0 \text{ V}; \text{ V}_{GS} = 10 \text{ V}$	-	19	-	nC
Q <sub>GS</sub>	gate-source charge	$I_D = 15 \text{ A}; V_{DS} = 50 \text{ V}; V_{GS} = 10 \text{ V};$	-	5	-	nC
Q <sub>GS(th)</sub>	pre-threshold gate-source charge	see Figure 14	-	3	-	nC
Q <sub>GS(th-pl)</sub>	post-threshold gate-source charge		-	2	-	nC
Q <sub>GD</sub>	gate-drain charge	$I_D$ = 15 A; $V_{DS}$ = 50 V; $V_{GS}$ = 10 V; see <u>Figure 14</u> and <u>15</u>	-	8	-	nC
V <sub>GS(pl)</sub>	gate-source plateau voltage	$V_{DS} = 50 \text{ V}$ ; see <u>Figure 14</u> and <u>15</u>	-	4.5	-	V
C <sub>iss</sub>	input capacitance	$V_{DS} = 50 \text{ V}; V_{GS} = 0 \text{ V}; f = 1 \text{ MHz};$	-	1847	-	pF
C <sub>oss</sub>	output capacitance	$T_j = 25 \text{ °C}; \text{ see } Figure 16$	-	86	-	pF
C <sub>rss</sub>	reverse transfer capacitance		-	64	-	pF
t <sub>d(on)</sub>	turn-on delay time	$V_{DS} = 50 \text{ V}; \text{ R}_{L} = 3.3 \Omega; \text{ V}_{GS} = 10 \text{ V};$	-	11	-	ns
t <sub>r</sub>	rise time	$R_{G(ext)} = 4.7 \ \Omega; T_j = 25 \ ^{\circ}C$	-	8	-	ns
t <sub>d(off)</sub>	turn-off delay time		-	22	-	ns
t <sub>f</sub>	fall time		-	7	-	ns

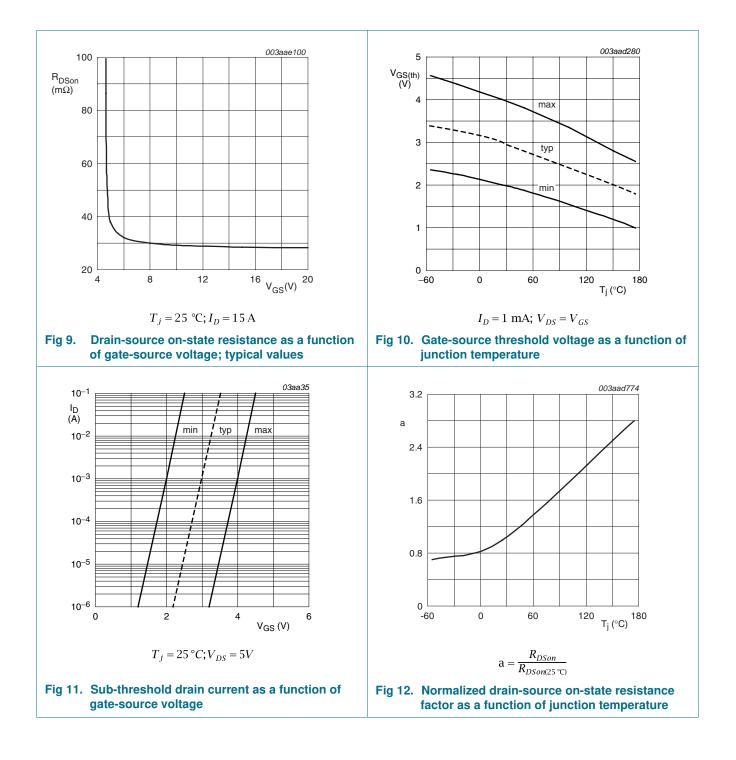
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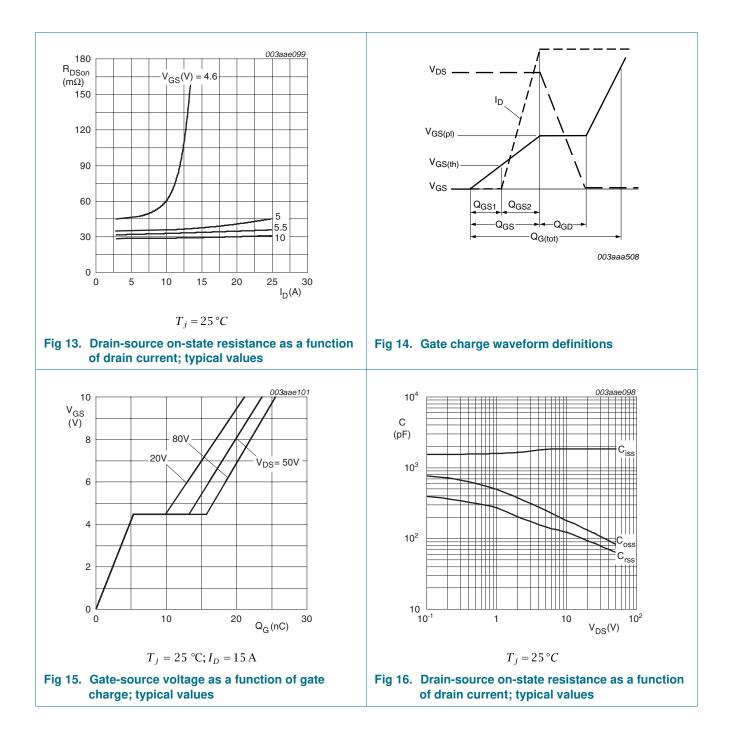
Table 6.	Characteristics continued						
Symbol	Parameter	Conditions	Min	Тур	Max	Unit	
Source-d	rain diode						
$V_{SD}$	source-drain voltage	I <sub>S</sub> = 15 A; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C; see <u>Figure 17</u>	-	0.8	1.2	V	
t <sub>rr</sub>	reverse recovery time	$I_{S} = 5 \text{ A}; dI_{S}/dt = 100 \text{ A}/\mu\text{s}; V_{GS} = 0 \text{ V};$	-	44	-	ns	
Qr	recovered charge	$V_{DS} = 50 V$	-	78	-	nC	



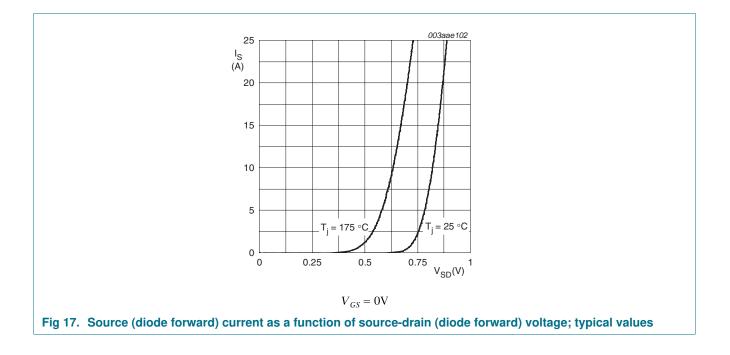
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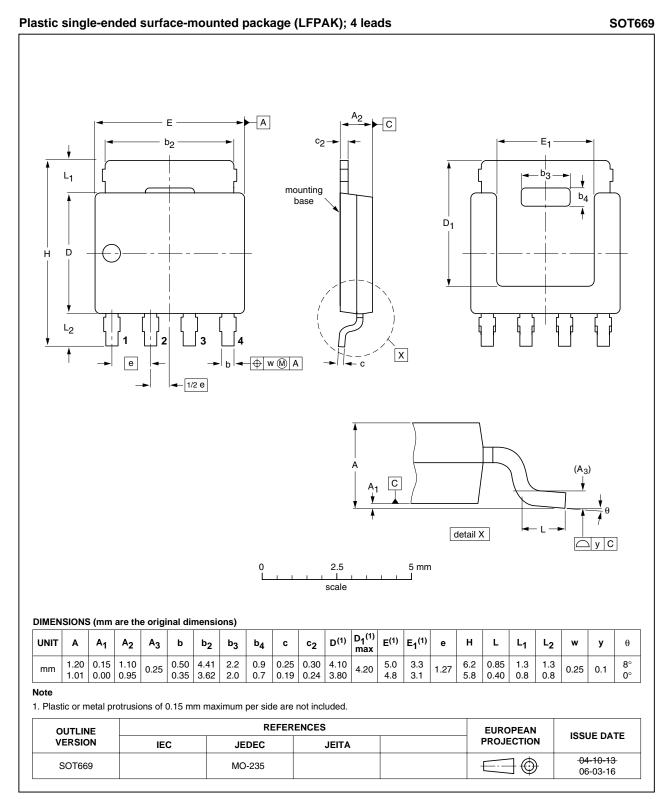


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### 7. Package outline



#### Fig 18. Package outline SOT669 (LFPAK)

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### 8. Revision history

Table 7.   Revision his	story			
Document ID	Release date	Data sheet status	Change notice	Supersedes
PSMN039-100YS_2	20100402	Product data sheet	-	PSMN039-100YS_1
Modifications:	<ul> <li>Status chail</li> </ul>	nged from Objective to P	roduct.	
PSMN039-100YS_1	20100114	Objective data sheet	-	-

### 9. Legal information

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Document status [1][2]	Product status <sup>[3]</sup>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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Product [short] data sheet	Production	This document contains the product specification.

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[2] The term 'short data sheet' is explained in section "Definitions".

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